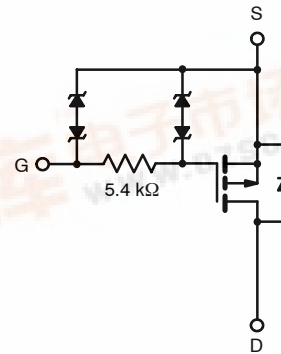
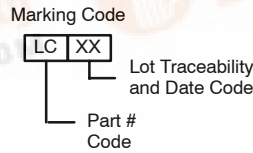
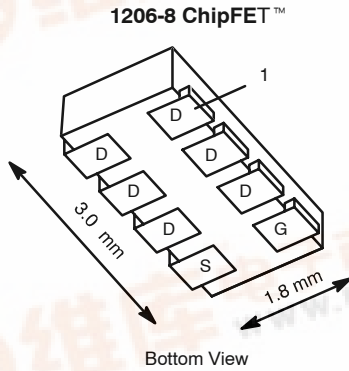




Si5465EDC
Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
-12	0.037 @ V _{GS} = -4.5 V	-7.0
	0.048 @ V _{GS} = -2.5 V	-6.1
	0.065 @ V _{GS} = -1.8 V	-5.2



P-Channel MOSFET

Ordering Information: Si5465EDC-T1

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V _{DS}	-12		V	
Gate-Source Voltage	V _{GS}	±12			
Continuous Drain Current (T _J = 150°C) ^a	I _D	T _A = 25°C	-7.0	-5.0	A
		T _A = 85°C	-5.0	-3.6	
Pulsed Drain Current	I _{DM}	-20			
Continuous Source Current ^a	I _S	-2.1	-1.1		
Maximum Power Dissipation ^a	P _D	T _A = 25°C	2.5	1.3	W
		T _A = 85°C	1.3	0.7	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{c, d}		260			

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 sec	40	50	°C/W
		Steady State	80	95	
Maximum Junction-to-Foot (Drain)	R _{thJF}	15	20		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. When using HBM. The MM rating is 300 V.
- c. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

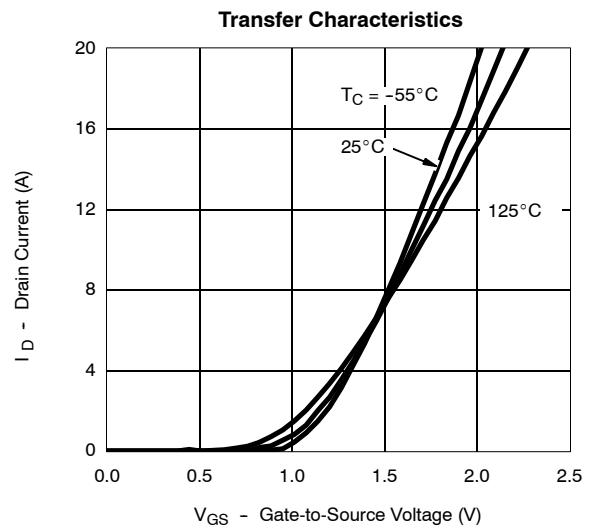
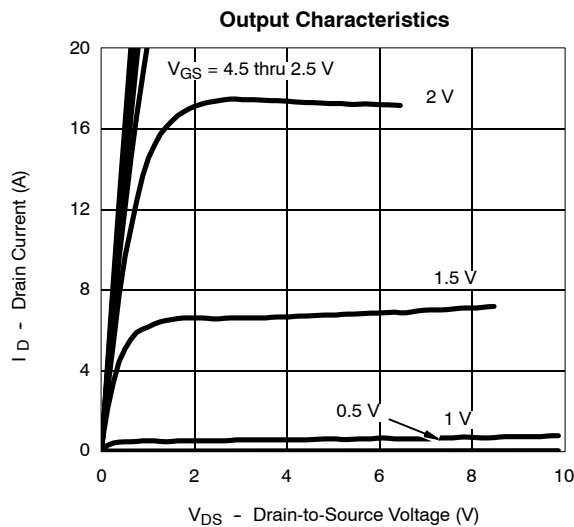


SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -1 mA	-0.45			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V			±1.5	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -9.6 V, V _{GS} = 0 V			-1	
		V _{DS} = -9.6 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -5.0 A		0.030	0.037	Ω
		V _{GS} = -2.5 V, I _D = -4.5 A		0.040	0.048	
		V _{GS} = -1.8 V, I _D = -2 A		0.052	0.065	
Forward Transconductance ^a	g _{fs}	V _{DS} = -5 V, I _D = -5.0 A		15		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1.1 A, V _{GS} = 0 V		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DD} = -6 V, V _{GS} = -4.5 V, I _D = -5.0 A		13.5	20	nC
Gate-Source Charge	Q _{gs}			2.8		
Gate-Drain Charge	Q _{gd}			4.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6 V, R _L = 6 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		2.5	3.5	μS
Rise Time	t _r			5.7	8.0	
Turn-Off Delay Time	t _{d(off)}			30	40	
Fall Time	t _f			21.5	30	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

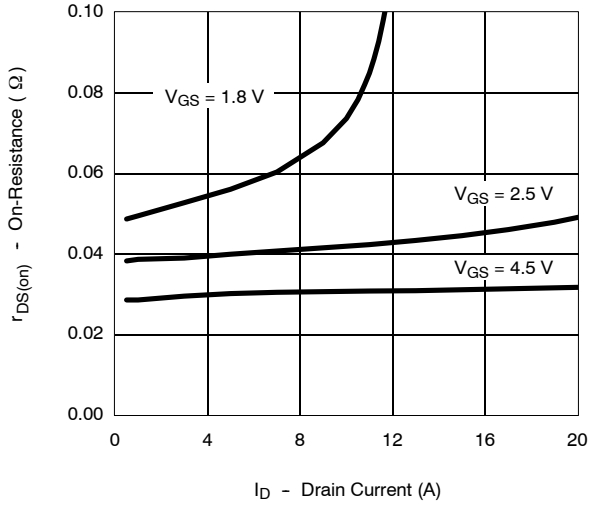
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



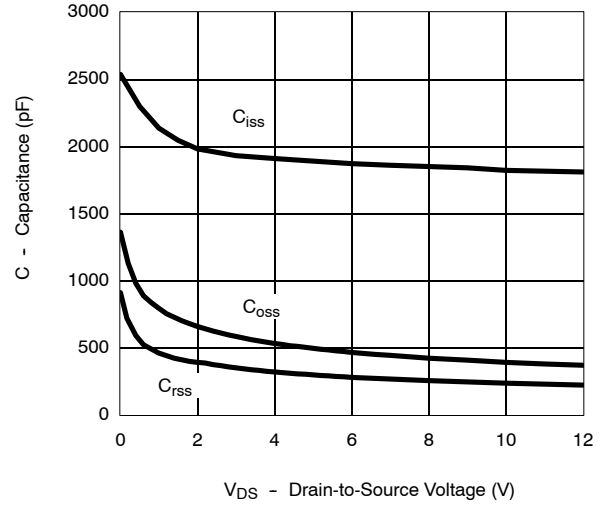


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

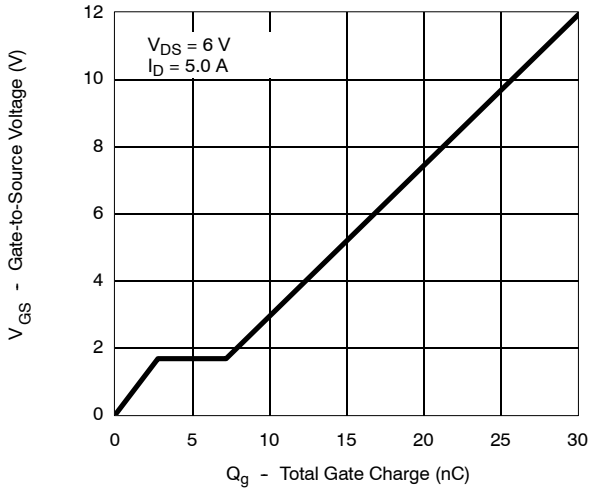
On-Resistance vs. Drain Current



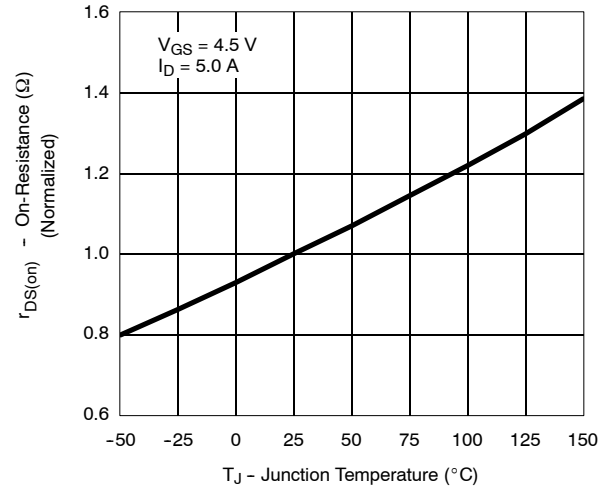
Capacitance



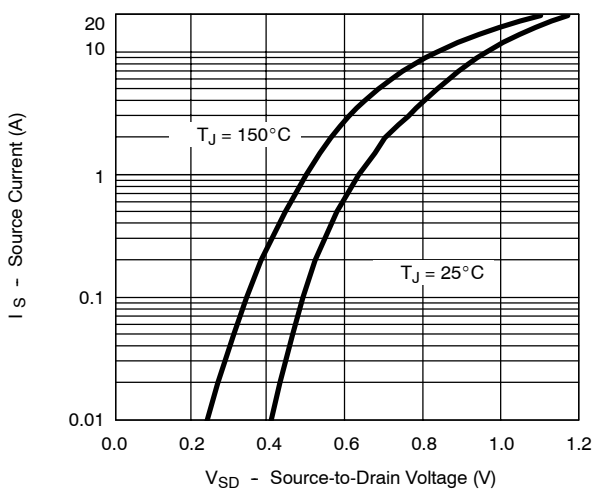
Gate Charge



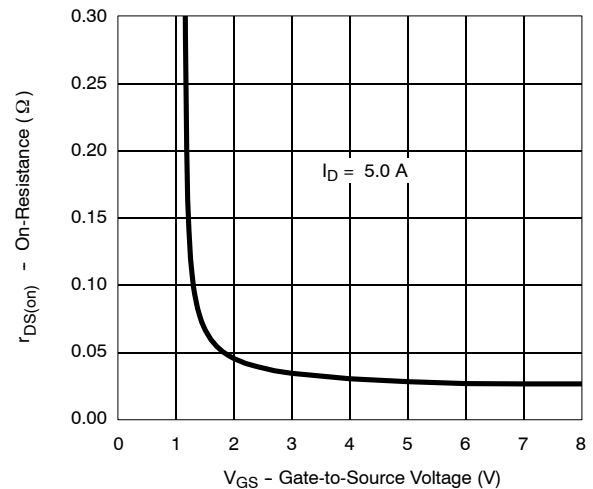
On-Resistance vs. Junction Temperature



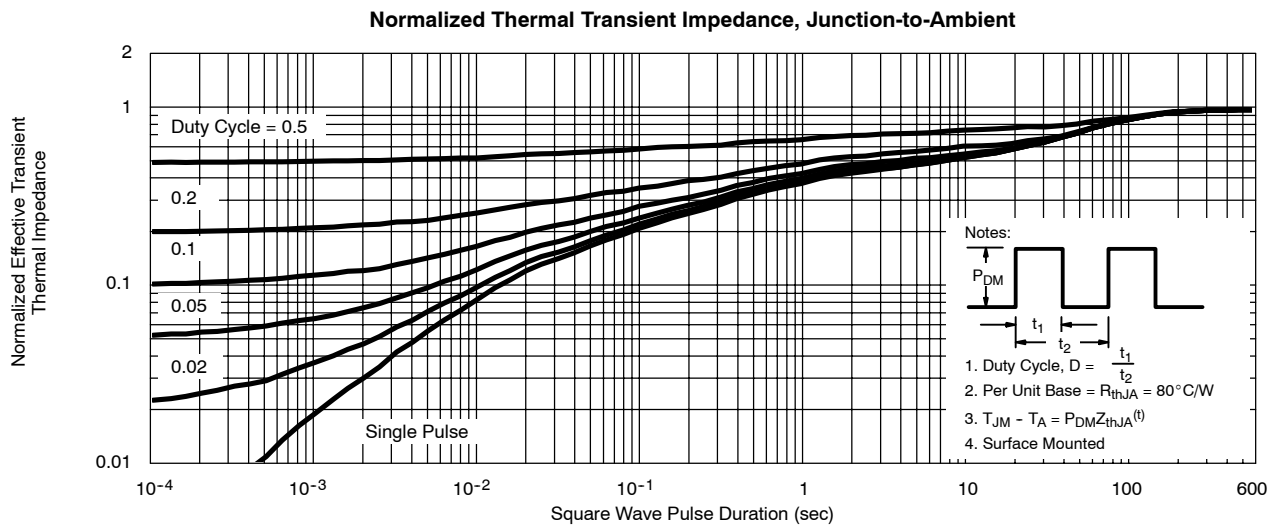
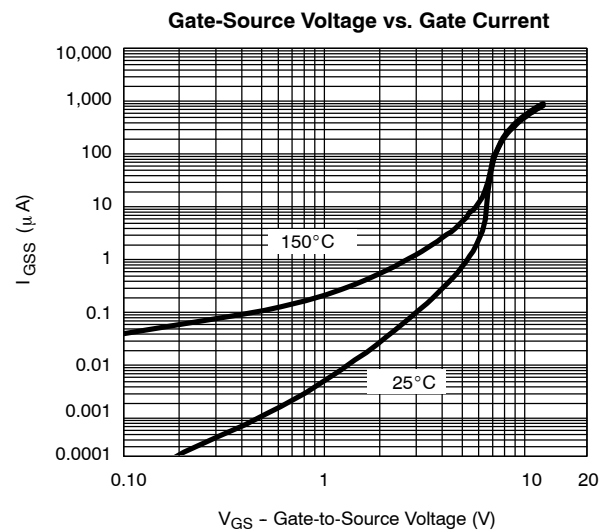
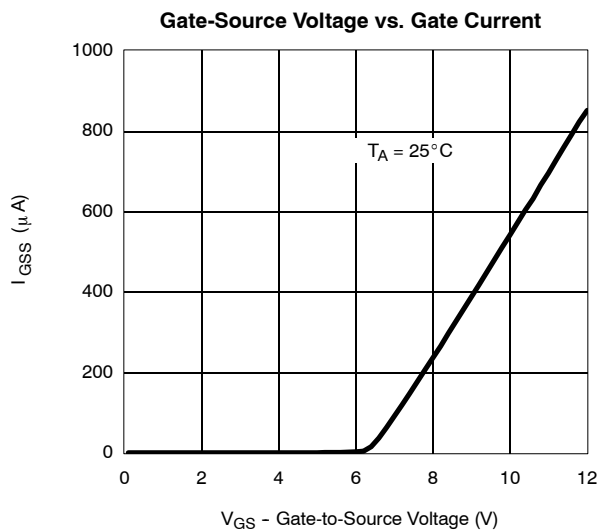
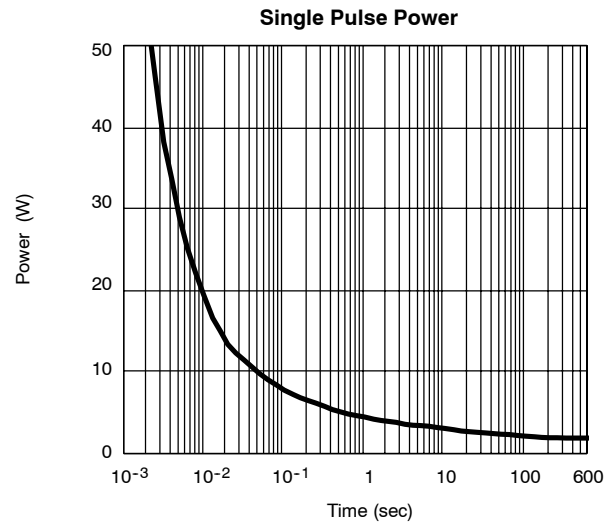
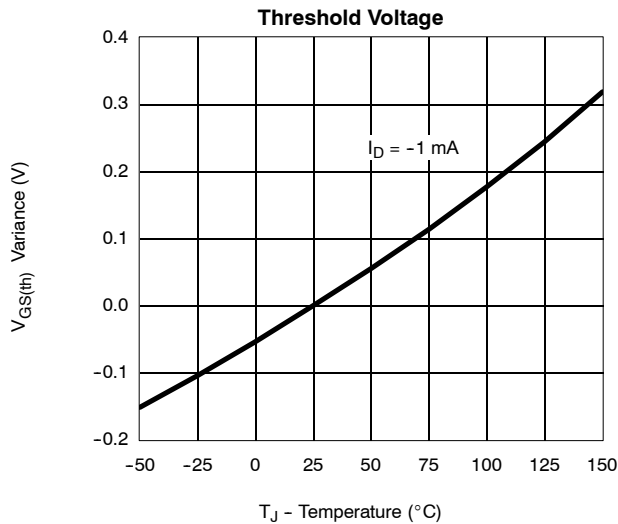
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

